International Rectifier

IR2304(S) & (PbF)

Features

- Floating channel designed for bootstrap operation to +600V. Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Under voltage lockout for both channels
- 3.3V, 5V, and 15V input logic input compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- Lower di/dt gate driver for better noise immunity
- Internal 100ns dead-time
- Output in phase with input
- Available in Lead-Free

Description

The IR2304(S) are a high voltage, high speed power MOSFET and IGBT driver with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies

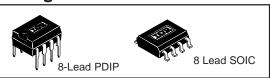
enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output driver features a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

HALF-BRIDGE DRIVER

Product Summary

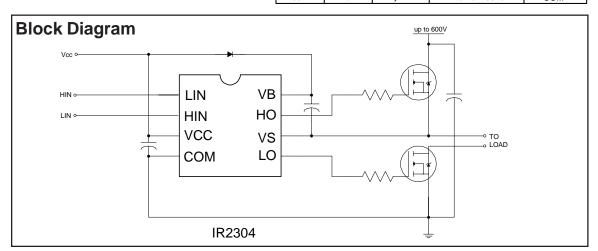
VOFFSET	600V max.
IO+/- (min)	60 mA/130 mA
Vout	10 - 20V
Delay Matching	50 ns
Internal deadtime	100 ns
ton/off (typ.)	220/220 ns

Package



2106/2301/2108/2109/2302/2304 Feature Comparison

				•		
Part	Input logic	Cross- conduction prevention logic	Dead-Time	Ground Pins		
2106/2301	HIN/LIN	no			none COM	
21064	HIIN/LIIN	110 Horie	VSS/COM			
2108	HIN/LIN yes		Internal 540ns	COM		
21084			Programmable 0.54~5μs	VSS/COM		
2109/2302	IN/SD	V00	Internal 540ns	COM		
21094	- IN/SD yes		Programmable 0.54~5μs	VSS/COM		
2304	HIN/LIN	yes	Internal 100ns	COM		



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
Vs	High side offset voltage		V _B - 25	V _B + 0.3	
V _B	High side floating supply voltage		-0.3	625	
V _{HO}	High side floating output voltage HO		V _S - 0.3	V _B + 0.3	
Vcc	Low side and logic fixed supply voltage		-0.3	25	V
V _{LO}	Low side output voltage LO		-0.3	V _{CC} + 0.3	
V _{IN}	Logic input voltage (HIN, LIN)		-0.3	V _{CC} + 0.3	
Com	Logic ground		V _{CC} -25	V _{CC} + 0.3	
dVs/dt	Allowable offset voltage SLEW RATE		_	50	V/ns
PD	Package power dissipation @ T _A ≤ +25°C 8-Lead SOIC		_	0.625	10/
		8-Lead PDIP	_	1.0	W
Rth _{JA}	Thermal resistance, junction to ambient 8-Lead SOIC 8-Lead PDIP		_	200	00004
			_	125	°C/W
TJ	Junction temperature		_	150	
T _S	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 seconds)			300	

Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply voltage	V _S + 10	V _S + 20	
Vs	High side floating supply offset voltage	Note 1	600	
Vно	High side (HO) output voltage	Vs	VB	.,
V _{LO}	Low side (LO) output voltage	COM	Vcc	v
V _{IN}	Logic input voltage (HIN, LIN)	COM	Vcc	
Vcc	Low side supply voltage	10	20	
TA	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of COM -5 to COM +600V. Logic state held for V_S of COM -5V to COM -V_{BS}.

Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and V_S is applicable to HO and LO.

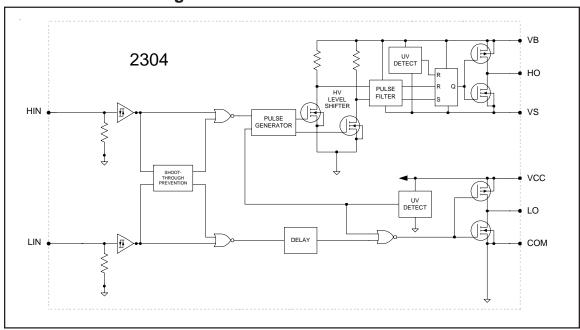
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{CCUV+} V _{BSUV+}	$V_{\mbox{CC}}$ and $V_{\mbox{BS}}$ supply undervoltage positive going threshold	8	8.9	9.8		
V _{CCUV} - V _{BSUV} -	V _{CC} and V _{BS} supply undervoltage negative going threshold	7.4	8.2	9	V	
V _{CCUVH} V _{BSUVH}	V _{CC} supply undervoltage lockout hysteresis	0.3	0.7	_		
I _{LK}	Offset supply leakage current	_	_	50		$V_{B} = V_{S} = 600V$
I _{QBS}	Quiescent V _{BS} supply current	20	60	150	μΑ	V _{IN} = 0V or 5V
IQCC	Quiescent V _{CC} supply current	50	120	240		V _{IN} = 0V or 5V
V _{IH}	Logic "1" input voltage	2.3	_	_		
V _{IL}	Logic "0" input voltage	_	_	0.8		
VoH	High level output voltage, V _{BIAS} - V _O	_	_	2.8	V	I _O = 20mA
V _{OL}	Low level output voltage, VO	_	_	1.2		
I _{IN+}	Logic "1" input bias current	_	5	40		V _{IN} = 5V
I _{IN-}	Logic "0" input bias current	_	1.0	2.0	μΑ	V _{IN} = 0V
I _{O+}	Output high short circuit pulse current	60	_	_	A	V _O = 0V
I _{O-}	Output low short circuit pulsed current	130	_	_	mA	PW ≤ 10 μs

Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{S} = COM, C_{L} = 1000 pF and T_{A} = 25°C unless otherwise specified.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay	120	220	320		V _S = 0V
toff	Turn-off propagation delay	130	220	330		V _S = 0V or 600V
t _r	Turn-on rise time	60	200	300		
tf	Turn-off fall time	20	100	170	ns	
DT	Dead time	80	100	190		
MT	Delay matching, HS & LS turn-on/off	_	_	50		

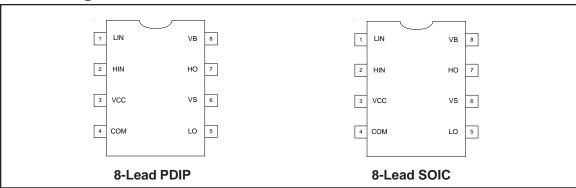
Functional Block Diagram



Lead Definitions

Symbol	Description
Vcc	Low side supply voltage
СОМ	Logic ground and low side driver return
HIN	Logic input for high side gate driver output
LIN	Logic input for low side gate driver output
VB	High side floating supply
НО	High side driver output
Vs	High voltage floating supply return
LO	Low side driver output

Lead Assignments



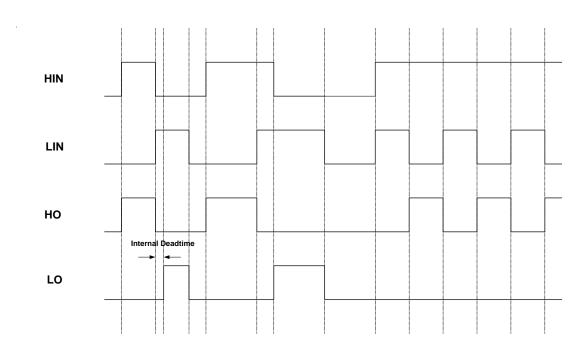


Figure 1. Input/Output Functionality Diagram

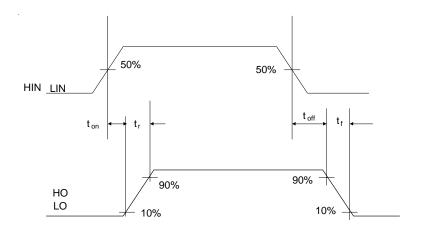


Figure 2. Switching Time Waveforms

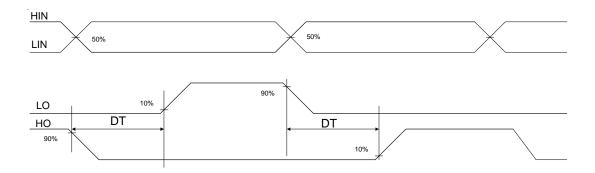
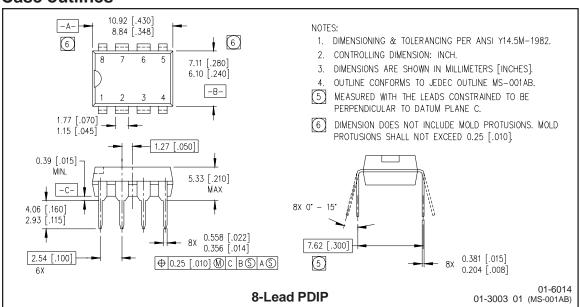


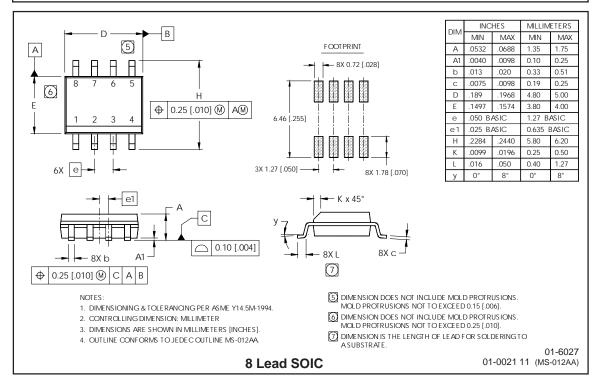
Figure 3. Internal Deadtime Timing

International TOR Rectifier

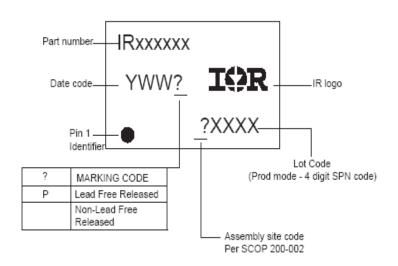
IR2304(S)&(PbF)

Case outlines





LEADFREE PART MARKING INFORMATION



ORDER INFORMATION

Basic Part (Non-Lead Free)

Lead-Free Part

8-Lead PDIP IR23	304 order IR2304	8-Lead PDIF	P IR2304	order IR2304PbF
8-Lead SOIC IR23	304S order IR2304	S 8-Lead SOIC	IR2304S	order IR2304SPbF



This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Web Site.

Data and specifications subject to change without notice.

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

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